NSN 5962-01-413-6857

Memory Microcircuit - Page 1 of 1



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Maximum Power Dissipation Rating:

1.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Agm-130/tvgs

Features Provided:

Electrostatic sensitive and ultraviolet erasable and monolithic and programmable

Inclosure Material:

Silicon

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Criticality Code Justification:

Cbbl

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit-eraseable programmable read only memory

Voltage Rating And Type Per Characteristic:

-0.5 volts total supply and 7.0 volts total supply

Time Rating Per Chacteristic:

55.00 nanoseconds access

Memory Device Type:

Eprom

Special Features:

Altered item, make from p/n 5962-8953702yx, dwg name microcircuits, memory, digital cmos, 16k x 8 uv eprom, monolithic silicon; endurance 25 cycles/byte,

Test Data Document:

96906-mil-std883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

28 printed circuit

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A458a0